

# FCD260N65S3

## MOSFET – Power, N-Channel, SUPERFET III, Easy Drive

650 V, 12 A, 260 mΩ

### Description

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate. Consequently, SUPERFET III MOSFET Easy drive series helps manage EMI issues and allows for easier design implementation.

### Features

- 700 V @  $T_J = 150^\circ\text{C}$
- Typ.  $R_{DS(on)} = 222\text{ m}\Omega$
- Ultra Low Gate Charge (Typ.  $Q_g = 24\text{ nC}$ )
- Low Effective Output Capacitance (Typ.  $C_{oss(eff.)} = 248\text{ pF}$ )
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

### Applications

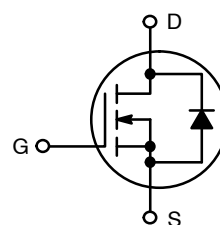
- Computing / Display Power Supplies
- Telecom / Server Power Supplies
- Industrial Power Supplies
- Lighting / Charger / Adapter



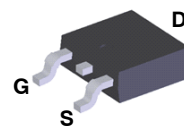
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$V_{DSS}$	$R_{DS(on)}\text{ MAX}$	$I_D\text{ MAX}$
650 V	260 mΩ @ 10 V	12 A

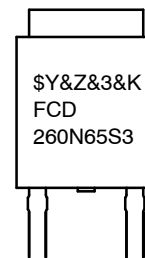


POWER MOSFET



D-PAK  
CASE 369AS

### MARKING DIAGRAM



\$Y = ON Semiconductor Logo  
&Z = Assembly Plant Code  
&3 = Data Code (Year & Week)  
&K = Lot  
FCD260N65S3 = Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# FCD260N65S3

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C, Unless otherwise specified)

Symbol	Parameter	Value	Unit
V <sub>DSS</sub>	Drain to Source Voltage	650	V
V <sub>GSS</sub>	Gate to Source Voltage	DC	±30
		AC (f > 1 Hz)	±30
I <sub>D</sub>	Drain Current	Continuous (T <sub>C</sub> = 25°C)	12
		Continuous (T <sub>C</sub> = 100°C)	7.6
I <sub>DM</sub>	Drain Current	Pulsed (Note 1)	30
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	57	mJ
I <sub>AS</sub>	Avalanche Current (Note 1)	2.3	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	0.9	mJ
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt (Note 3)	20	
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C)	90
		Derate Above 25°C	0.72
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 s	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. I<sub>AS</sub> = 2.3 A, R<sub>G</sub> = 25 Ω, starting T<sub>J</sub> = 25°C.
3. I<sub>SD</sub> ≤ 6 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ 400 V, starting T<sub>J</sub> = 25°C.

## THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction to Case, Max.	1.39	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient, Max. (Note 4)	40	

4. Device on 1 in<sup>2</sup> pad 2 oz copper pad on 1.5 x 1.5 in. board of FR-4 material.

## PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Reel Size	Tape Width	Shipping†
FCD260N65S3	FCD260N65S3	D-PAK	330 mm	16 mm	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# FCD260N65S3

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA, T <sub>J</sub> = 25°C	650			V
		V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA, T <sub>J</sub> = 150°C	700			V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 1 mA, Referenced to 25°C		0.66		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 520 V, T <sub>C</sub> = 125°C		0.77		
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V			±100	nA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 0.29 mA	2.5		4.5	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6 A		222	260	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 6 A		7.4		S

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V, f = 1 MHz		1010		pF
C <sub>oss</sub>	Output Capacitance			25		pF
C <sub>oss(eff.)</sub>	Effective Output Capacitance	V <sub>DS</sub> = 0 V to 400 V, V <sub>GS</sub> = 0 V		248		pF
C <sub>oss(er.)</sub>	Energy Related Output Capacitance	V <sub>DS</sub> = 0 V to 400 V, V <sub>GS</sub> = 0 V		33		pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10 V	V <sub>DS</sub> = 400 V, I <sub>D</sub> = 6 A, V <sub>GS</sub> = 10 V (Note 5)		24		nC
Q <sub>gs</sub>	Gate to Source Gate Charge			6.1		nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge			9.7		nC
ESR	Equivalent Series Resistance	f = 1 MHz		8.7		Ω

### SWITCHING CHARACTERISTICS

t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 400 V, I <sub>D</sub> = 6 A, V <sub>GS</sub> = 10 V, R <sub>g</sub> = 4.7 Ω (Note 5)		18		ns
t <sub>r</sub>	Turn-On Rise Time			18		ns
t <sub>d(off)</sub>	Turn-Off Delay Time			49		ns
t <sub>f</sub>	Turn-Off Fall Time			12		ns

### SOURCE-DRAIN DIODE CHARACTERISTICS

I <sub>S</sub>	Maximum Continuous Source to Drain Diode Forward Current			12		A
I <sub>SM</sub>	Maximum Pulsed Source to Drain Diode Forward Current			30		A
V <sub>SD</sub>	Source to Drain Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 6 A			1.2	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>DD</sub> = 400 V, I <sub>SD</sub> = 6 A, dI <sub>F</sub> /dt = 100 A/μs		251		ns
Q <sub>rr</sub>	Reverse Recovery Charge			3.4		μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

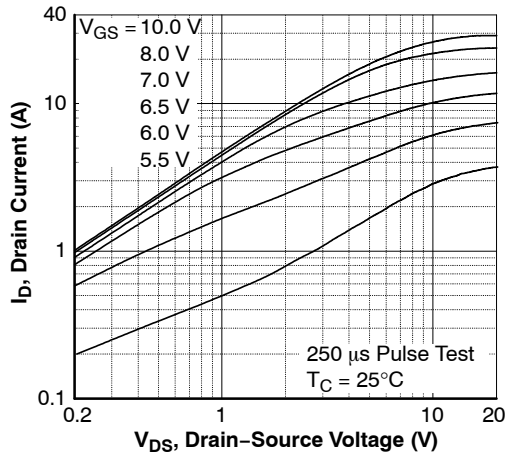


Figure 1. On-Region Characteristics

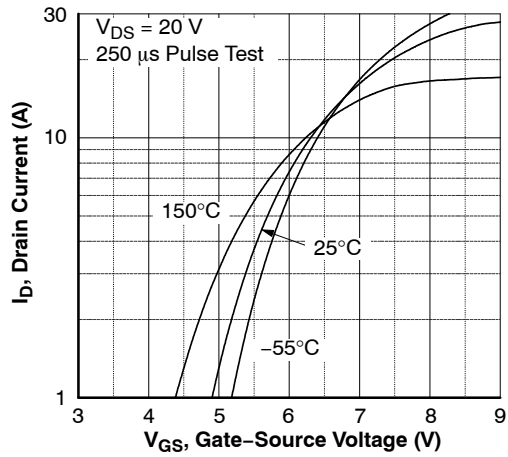


Figure 2. Transfer Characteristics

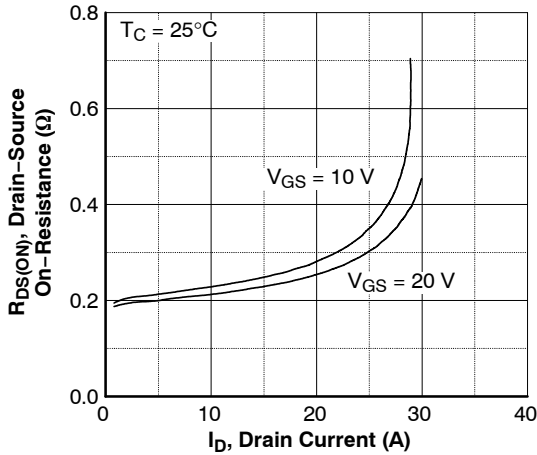


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

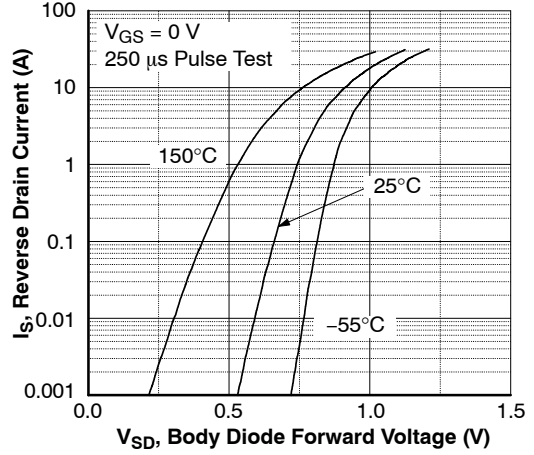


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

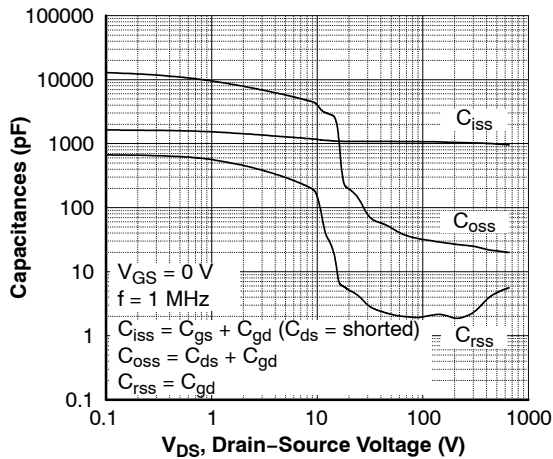


Figure 5. Capacitance Characteristics

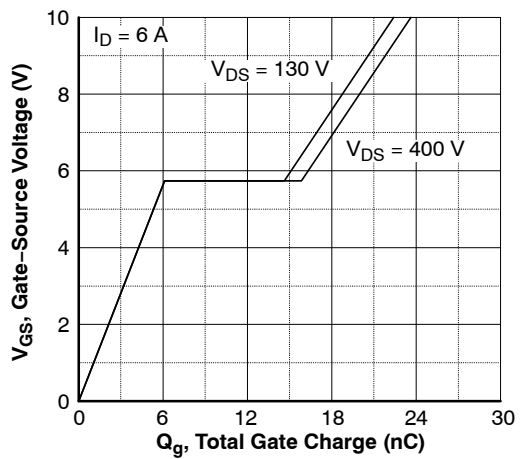


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

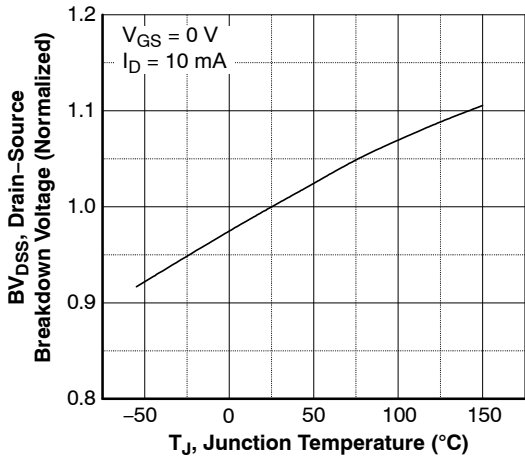


Figure 7. Breakdown Voltage Variation vs. Temperature

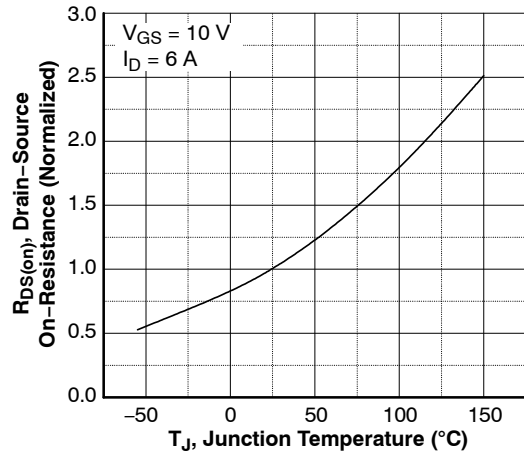


Figure 8. On-Resistance Variation vs. Temperature

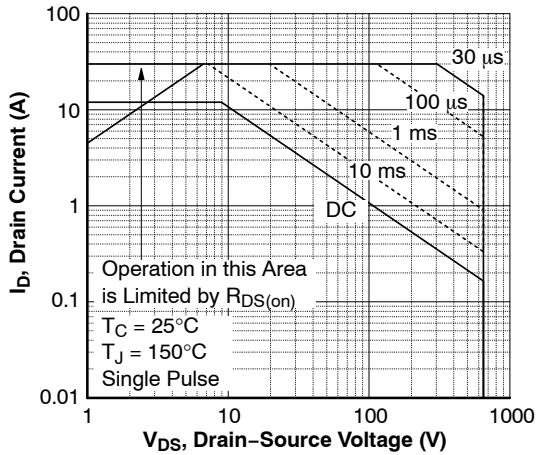


Figure 9. Maximum Safe Operating Area

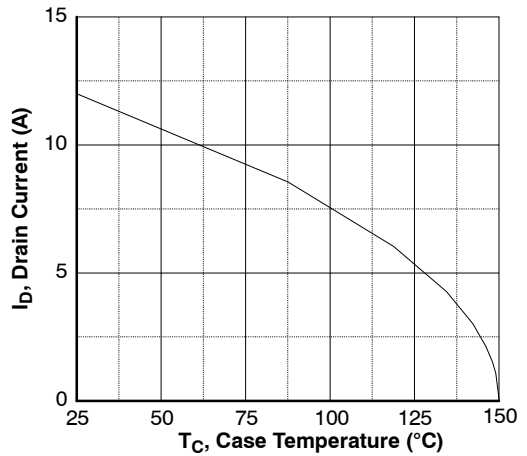


Figure 10. Maximum Drain Current vs. Case Temperature

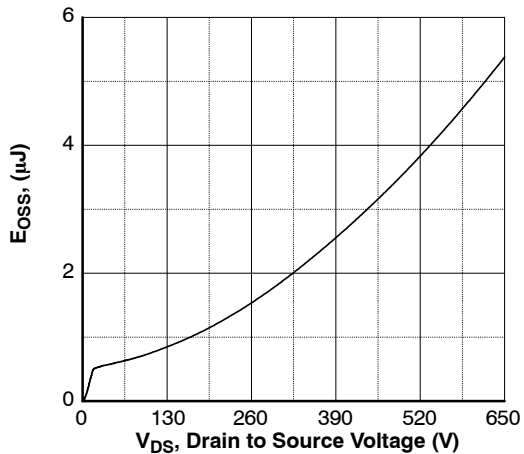


Figure 11. E<sub>OSS</sub> vs. Drain to Source Voltage

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## TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

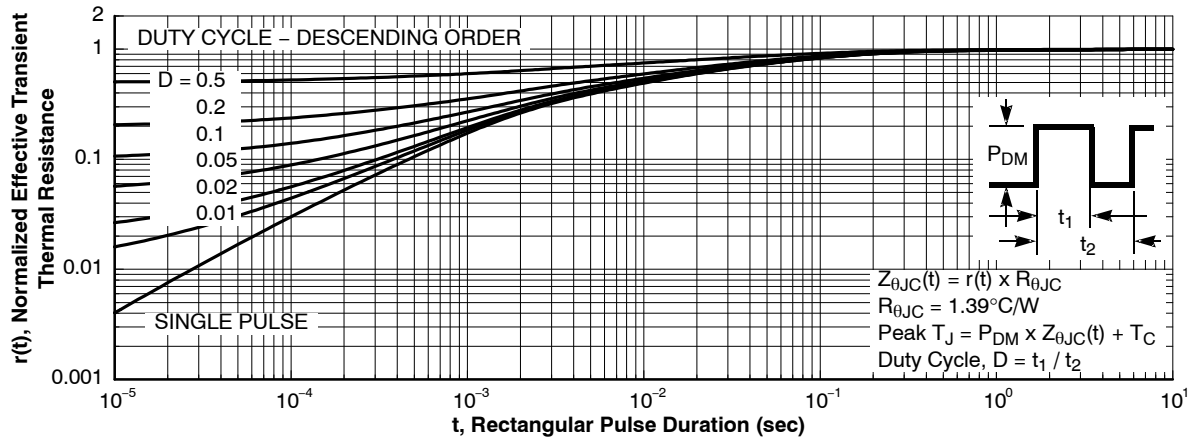


Figure 12. Transient Thermal Response Curve



Figure 13. Gate Charge Test Circuit & Waveform

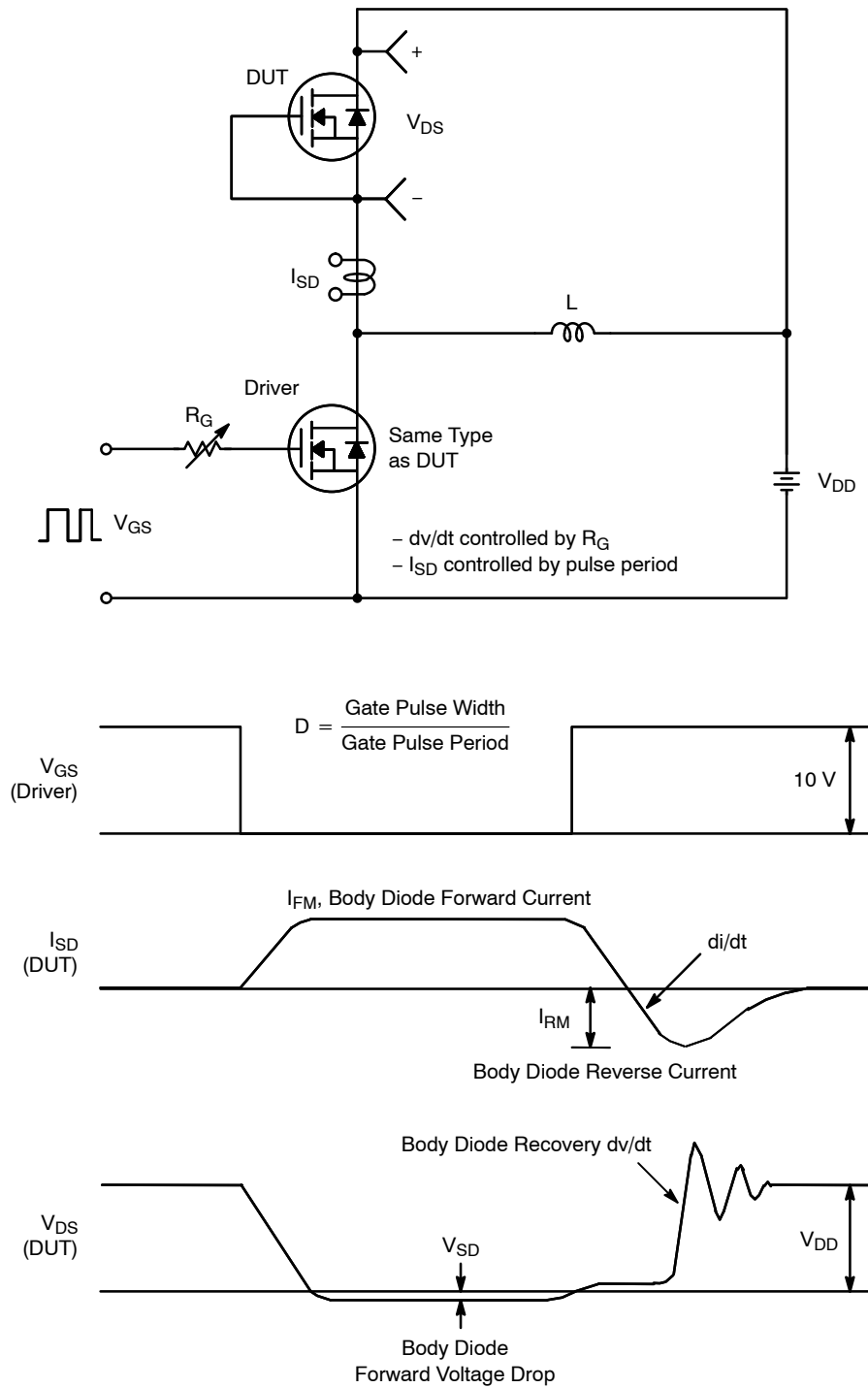


Figure 14. Resistive Switching Test Circuit & Waveforms



Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

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**Figure 16. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms**



# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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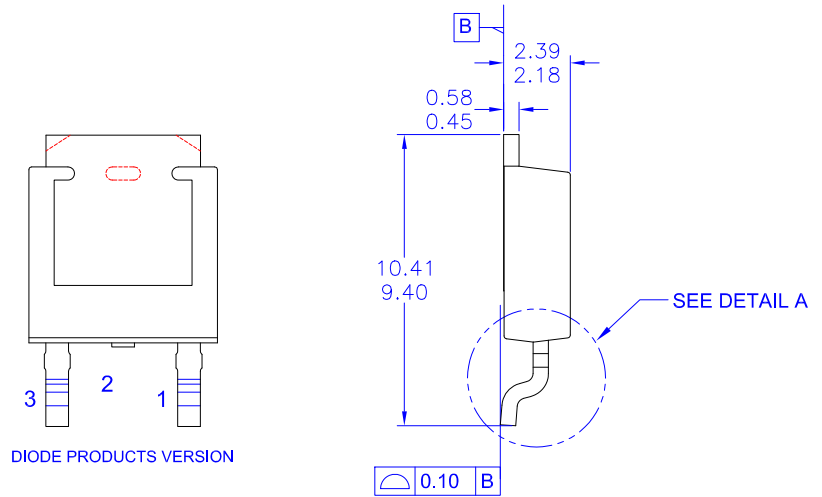
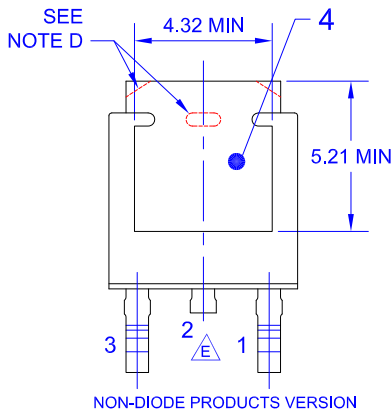
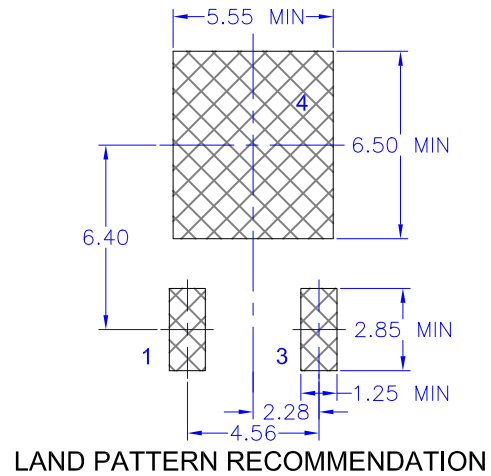
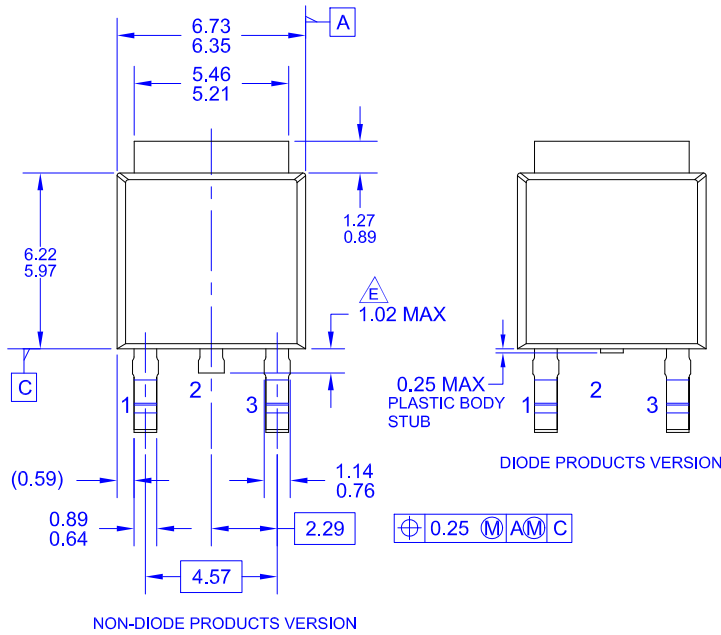


### DPAK3 (TO-252 3 LD)

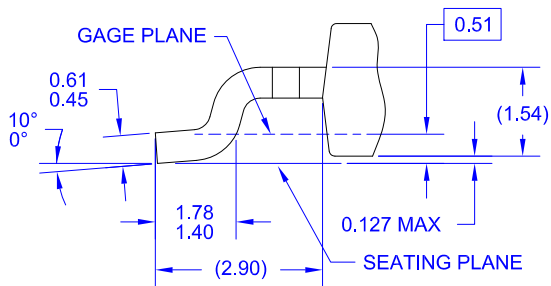
#### CASE 369AS

#### ISSUE O

DATE 30 SEP 2016



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
  - B) ALL DIMENSIONS ARE IN MILLIMETERS.
  - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
  - D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
  - E) TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS
  - F) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
  - G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.



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